

General Description

The ZMS100N10S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

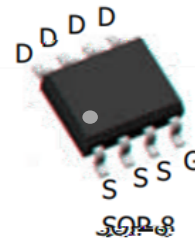
Features

Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

Application

nd Synchronous Rectifier

Product Summary



Ordering Information:

Part NO.	
Marking	
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25$	12	A
	$I_D @ T_C = 75$	10.6	A
	$I_D @ T_C = 100$	8.8	A
Pulsed Drain Current	I_{DM}	42	A
Total Power Dissipation	$P_D @ T_C = 25$	3.1	W
Total Power Dissipation	$P_D @ T_A = 25$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy @ $L = 0.1mH$	E_{AS}	45	mJ



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	40	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	180	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
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